



Attorney Docket No. ASC-023DVC2
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Eugene A. Fitzgerald

Application No. 10/022,689

Filed: December 17, 2001

Art Unit: 2813

Title: CONTROLLING THREADING
DISLOCATION DENSITIES IN GE ON SI
USING GRADED GESI LAYERS AND
PLANARIZATION

Examiner: Laura Schillinger

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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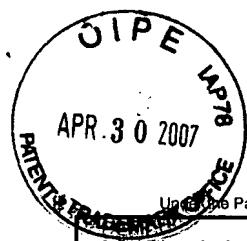
It is respectfully requested that the references listed on the attached Form PTO/SB/08, and other information contained herein, be made of record in this application.

Dated: *April 25, 2007*

Respectfully submitted,

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				First Named Inventor	Eugene A. Fitzgerald
				Art Unit	2813
				Examiner Name	Laura Schillinger
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U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)	MM-DD-YYYY		
A1	US-4,704,302	11-03-1987	Bruel et al.		
A2	US-5,405,802	04-11-1995	Yamagata et al.		
A3	US-5,426,316	06-20-1995	Mohammad		
A4	US-5,705,421	01-06-1998	Matsushita et al.		

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
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